

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.7mΩ@10V	275A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

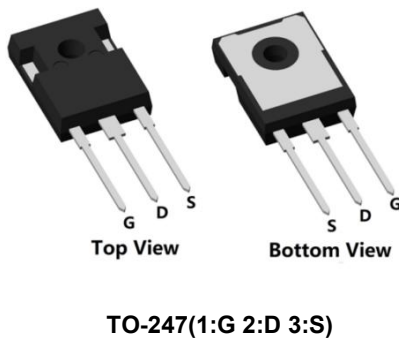
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

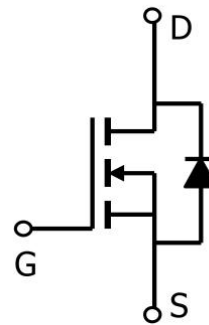
Applications

- Power switching application
- DC-DC Converter
- Power Management

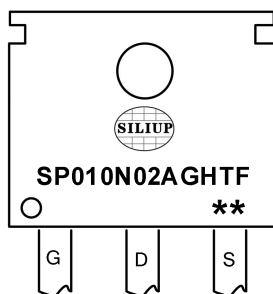
Package



Circuit diagram



Marking



SP010N02AGHTF : Product code
** : Week code

Order Information

Device	Package	Unit/Tube
SP010N02AGHTF	TO-247	30

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	Silicon Limit	I_D	300	A
Continuous Drain Current (Tc=25°C)	Package Limit	I_D	275	A
Continuous Drain Current (Tc=100°C)		I_D	183	A
Pulsed Drain Current		I_{DM}	1100	A
Single Pulse Avalanche Energy ¹		E_{AS}	2025	mJ
Power Dissipation (Tc=25°C)		P_D	300	W
Power Dissipation (Tc=100°C)		P_D	120	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	0.42	°C/W
Storage Temperature Range		T_{STG}	-55 to 150	°C
Operating Junction Temperature Range		T_J	-55 to 150	°C

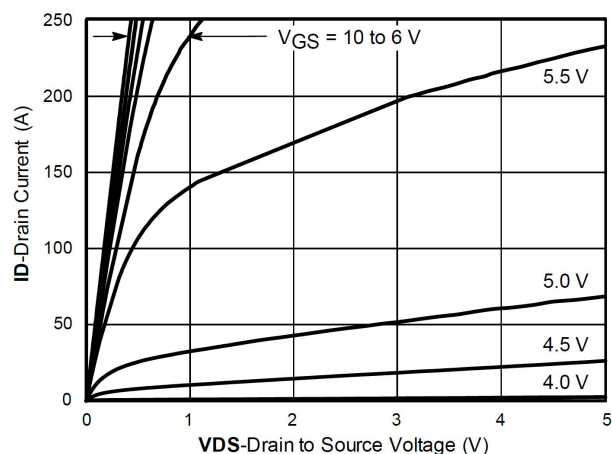
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	100	-	-	V
Drain Cut-Off Current	IDSS	VDS=80V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2.6	3.0	3.4	V
Drain-Source ON Resistance	RDS(ON)	VGS=10V , ID=20A	-	1.7	2.15	mΩ
Gate Resistance	RG	VDS=50V , VGS=0V , f=1MHz	-	3.4	-	Ω
Dynamic Characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	-	9499	-	pF
Output Capacitance	Coss		-	3765	-	
Reverse Transfer Capacitance	Crss		-	86	-	
Total Gate Charge	Qg	VDS=50V , VGS=10V , ID=100A	-	152	-	nC
Gate-Source Charge	Qgs		-	42	-	
Gate-Drain Charge	Qgd		-	32	-	
Gate Plateau Voltage	Vplateau		-	5	-	V
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=50V , VGS=10V , RG=4Ω , ID=100A	-	20	-	nS
Rise Time	tr		-	60	-	
Turn-Off Delay Time	td(off)		-	70	-	
Fall Time	tr		-	23	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	IS=1A , VGS=0V	-	-	1.2	V
Maximum Body-Diode Continuous Current	Is		-	-	275	A
Reverse Recovery Time	Trr	IS=50A , di/dt=100A/us , TJ=25℃	-	96	-	nS
Reverse Recovery Charge	Qrr		-	196	-	nC

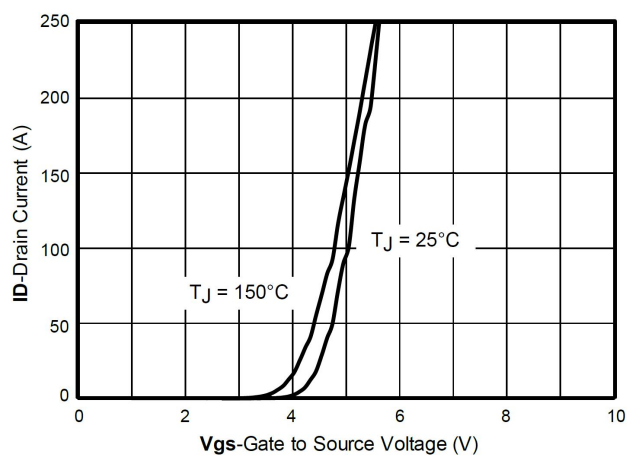
Note :

1. The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

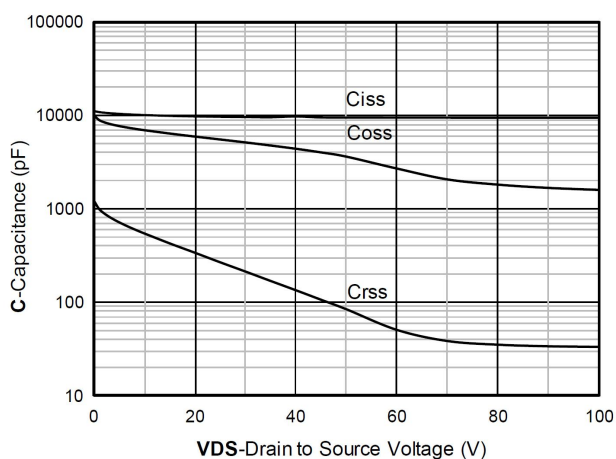
Typical Characteristics



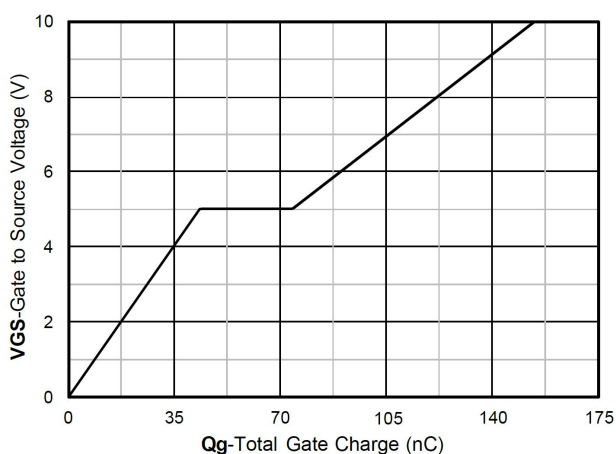
Output Characteristics



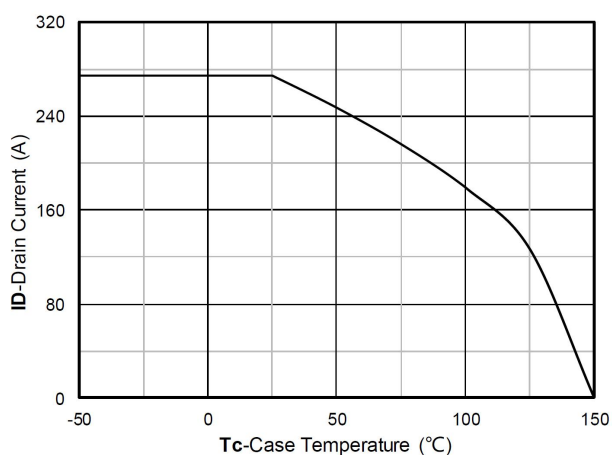
Transfer Characteristics



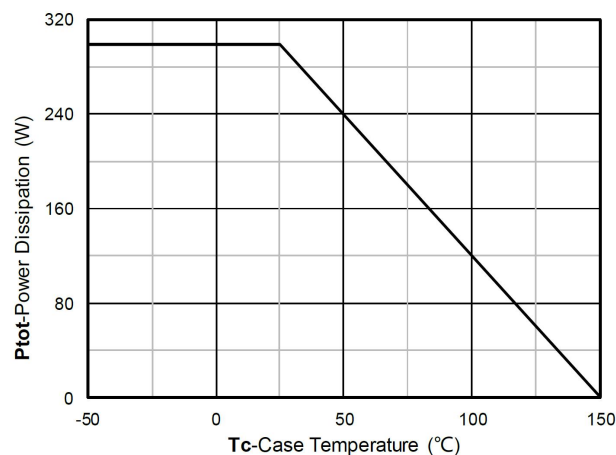
Capacitance Characteristics



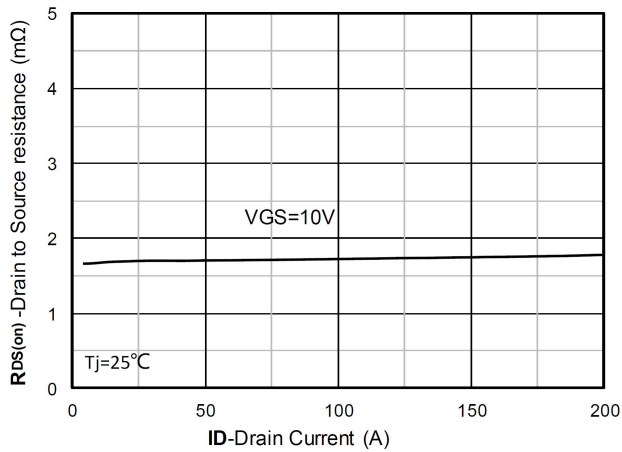
Gate Charge



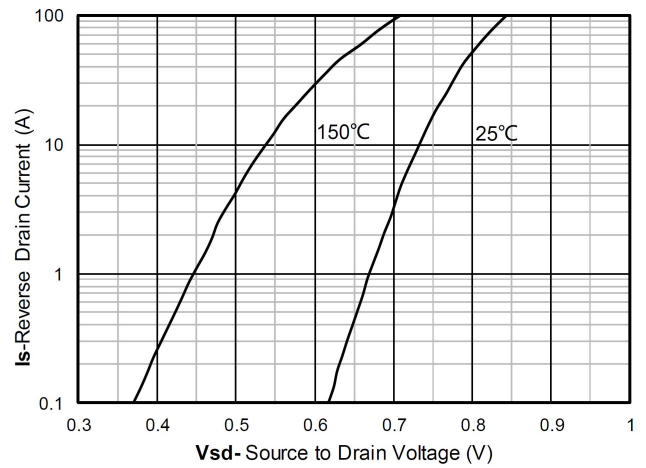
Current dissipation



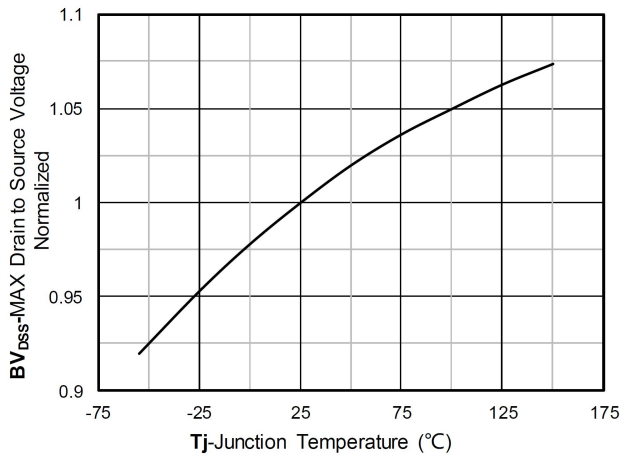
Power dissipation



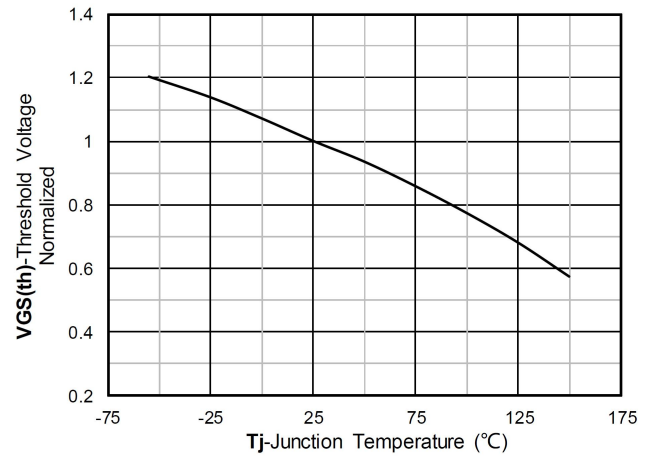
$R_{DS(on)}$ VS Drain Current



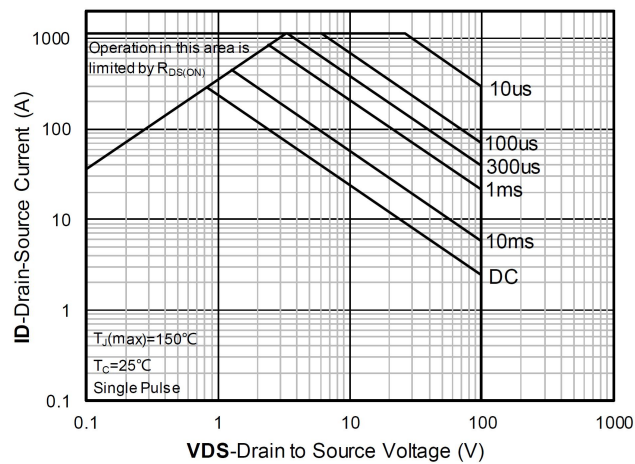
Forward characteristics of reverse diode



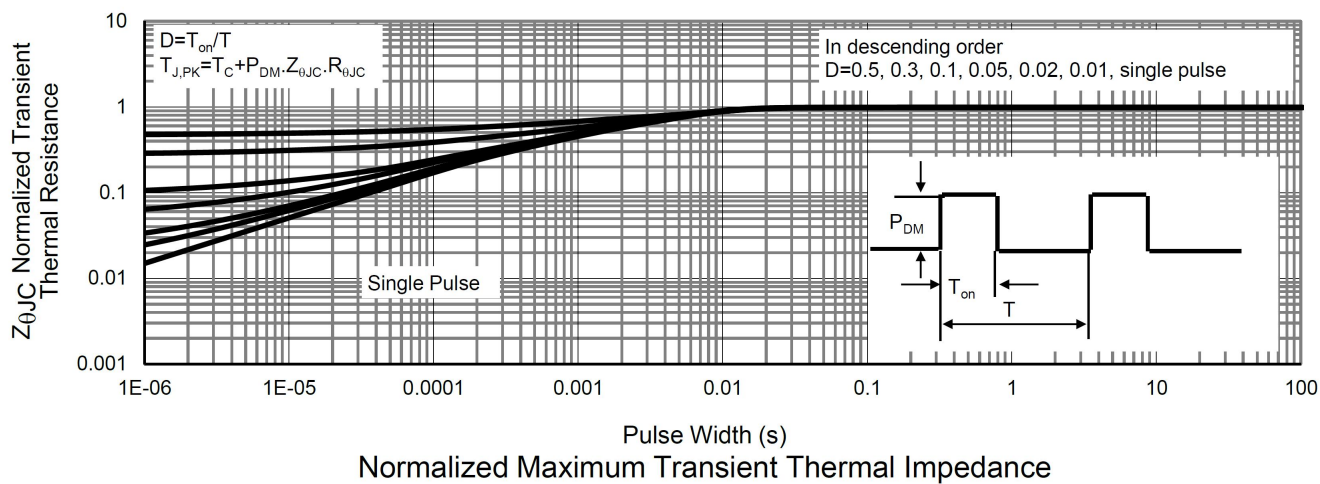
Normalized breakdown voltage



Normalized Threshold voltage

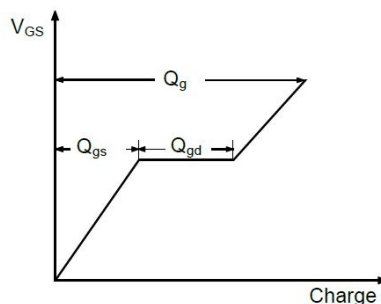
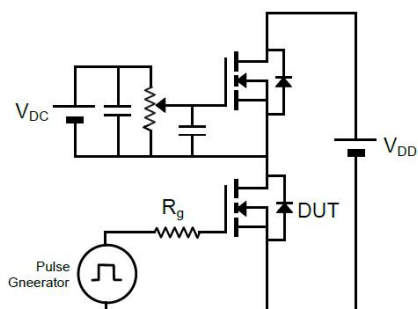


Safe Operation Area

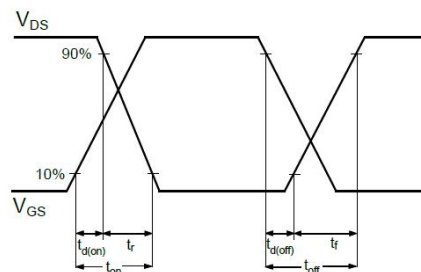
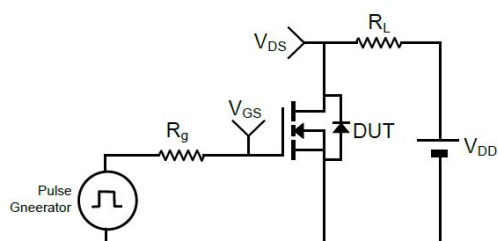


Test Circuit

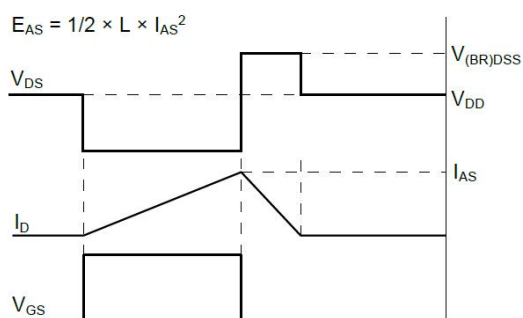
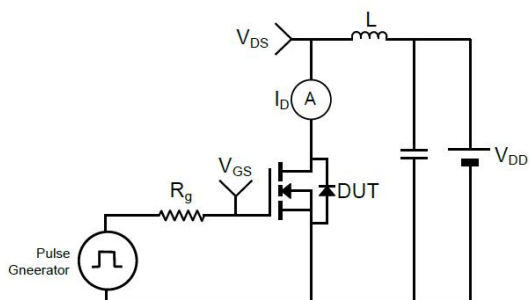
Gate Charge



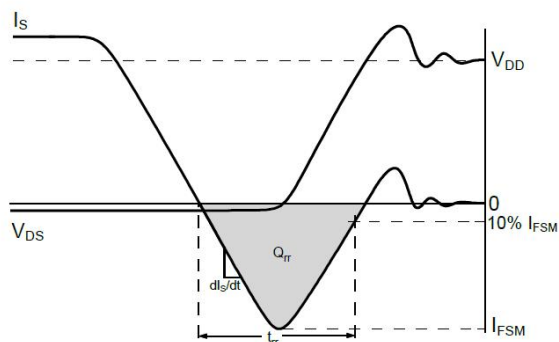
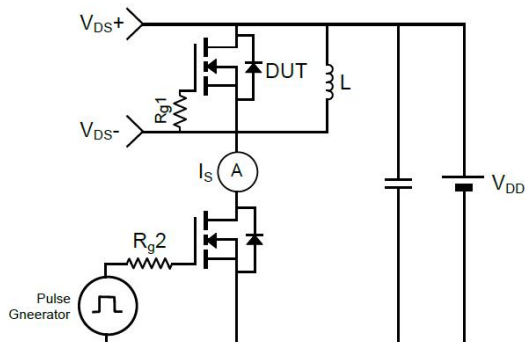
Resistive Load Switching Time



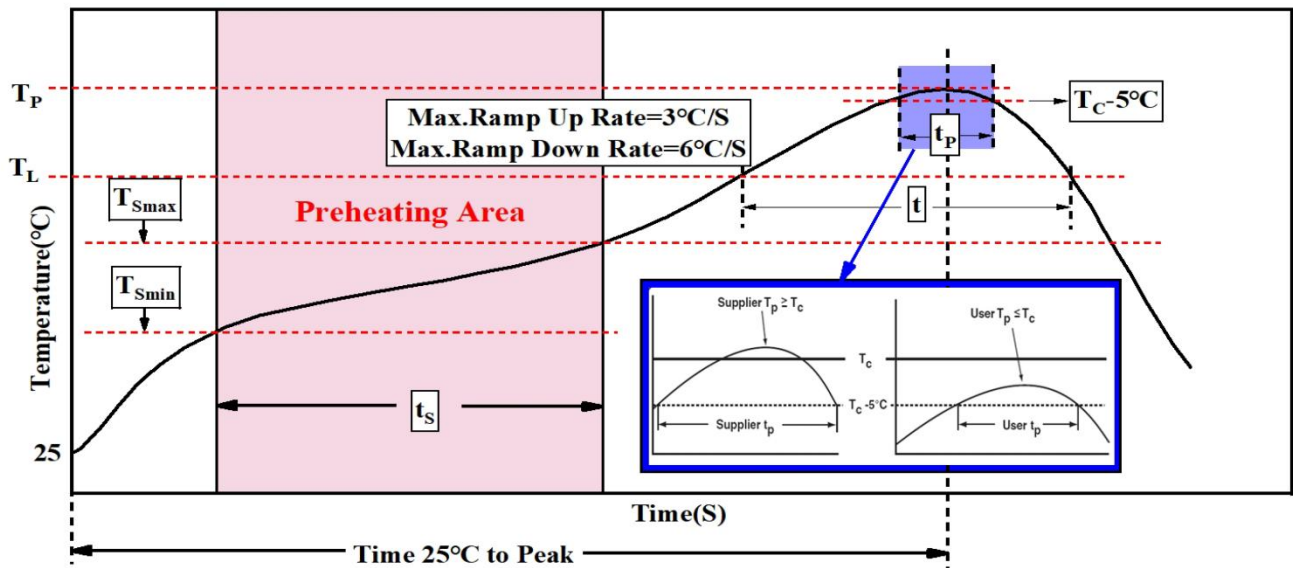
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering(Pb-Free)



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{min})	100°C	150°C
Temperature max (T _{max})	150°C	200°C
Time (T _{min} to T _{max}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{max} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{max})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

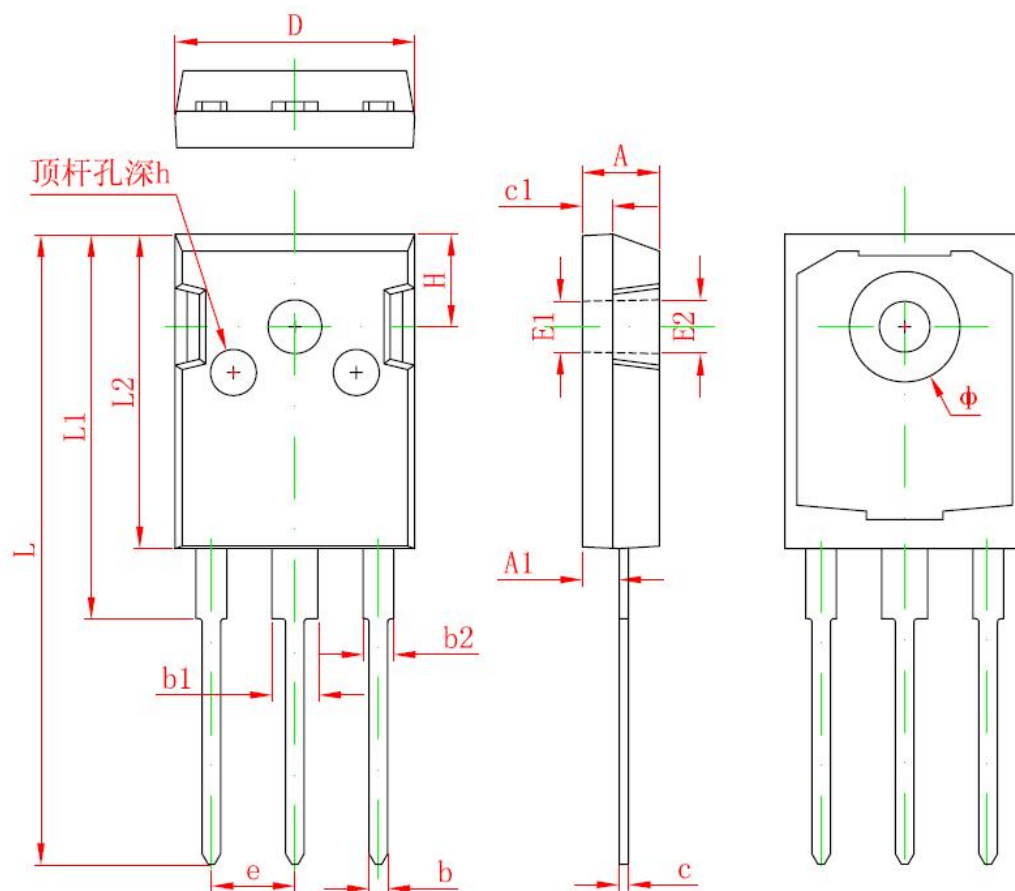
Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C



TO-247 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.700	5.300
A1	2.100	2.600
b	1.000	1.400
b1	2.800	3.200
b2	1.800	2.200
c	0.500	0.700
c1	1.900	2.500
D	15.450	16.200
E1	3.500 REF.	
E2	3.600 REF.	
L	40.400	41.600
L1	24.750	25.750
L2	20.300	21.300
Φ	7.100	7.300
e	5.450 TYP.	
H	5.980 REF.	
h	0.000	0.300